

Comparative Evaluation of SiO₂ Atomic Layer Etching Using NF₃ and SF₆ Gases via a Combined Thermal and Remote Plasma Approach

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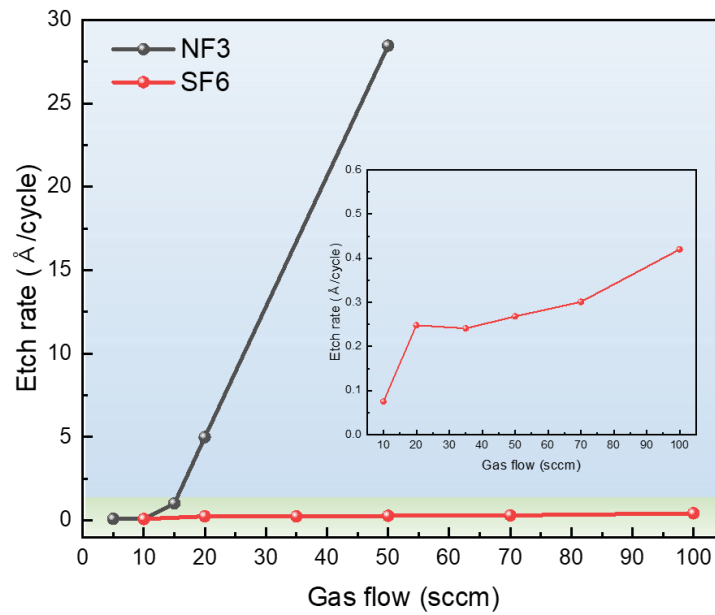


Figure 1. Etch rate as a function of gas flow rate for NF₃ (black) and SF₆ (red). The green shaded area represents etch rates corresponding to the atomic layer etching (ALE) regime, while the blue area indicates the conventional plasma etching regime, characterized by higher EPC. The inset shows an enlarged view of the SF₆ etch rate.

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